

Product Overview

NGTB40N120FL3: IGBT, Ultra Field Stop -1200V 40A

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Ultra Field Stop Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for UPS and solar applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- Extremely Efficient Trench with Ultra Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for High Speed Switching
- These are Pb-Free Devices

Applications

- Solar Inverter
- Uninterruptible Power Inverter Supplies (UPS)
- Welding

End Products

- Industrial

Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	I_C Max (A)	$V_{GE}^{(sa)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μs)	E_{AS} Typ (mJ)	P_D Max (W)	Co- Pack aged Diode	Pack age Type
NGTB40N120FL3WG	Pb-free Halide free	Active	1200	40	1.7	3	1.1	1.6	86	12	212	-	-	454	Yes	TO-247-3

For more information please contact your local sales support at www.onsemi.com.

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